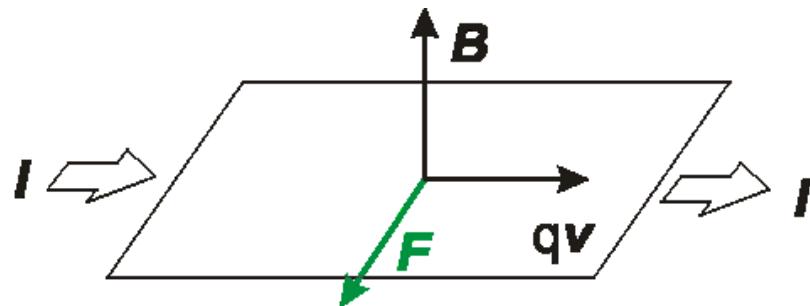
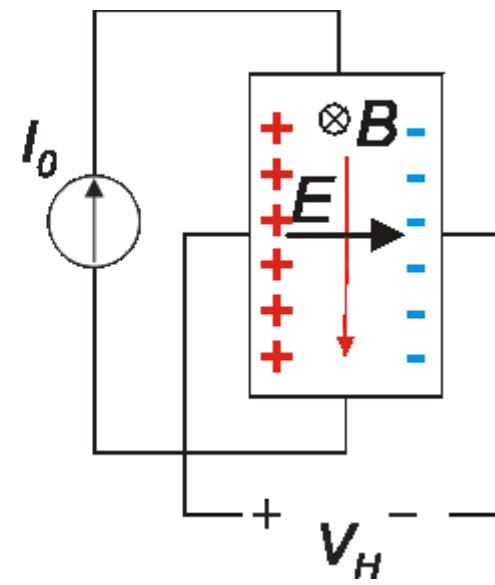
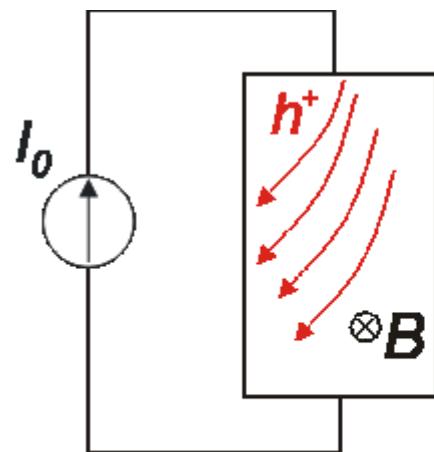
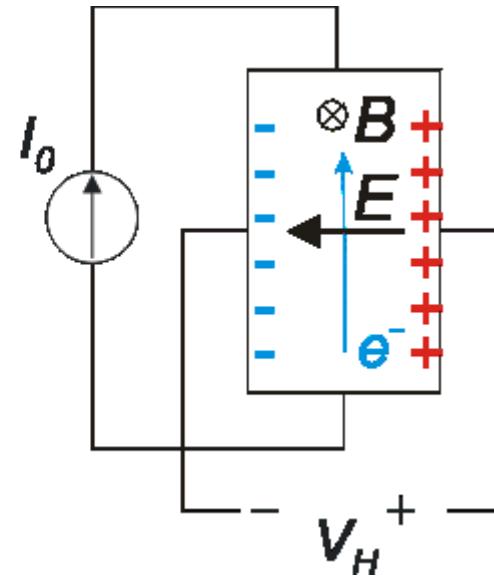
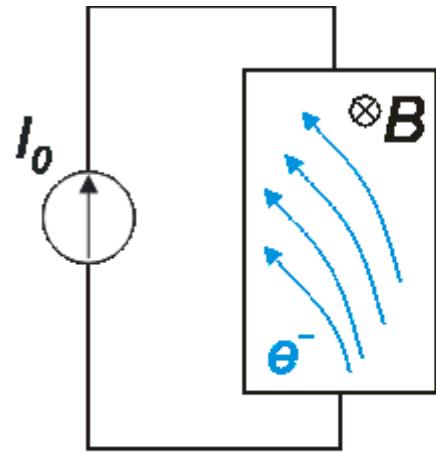


# Magnetic Sensors

## 1) Hall sensors

Hall effect: Discovered by Edwin Hall in 1879





# Resistive Magnetic Sensors

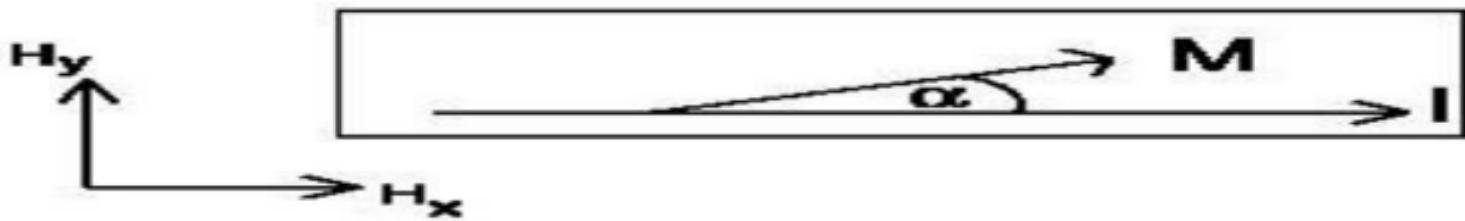
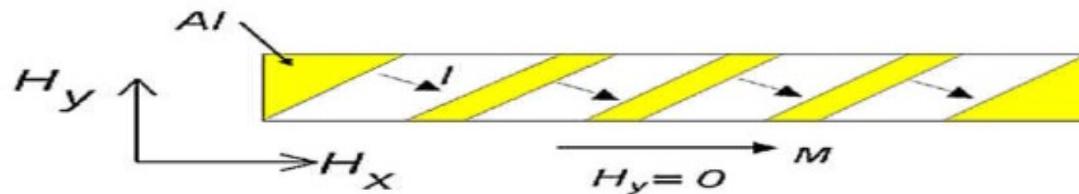


Fig. 1: The geometry of a Hunt element

› change in resistivity is found experimentally to be

$$R = R_0 \cdot \left(1 + \frac{\Delta R}{R} \cdot \cos^2 \alpha\right) \quad (1)$$

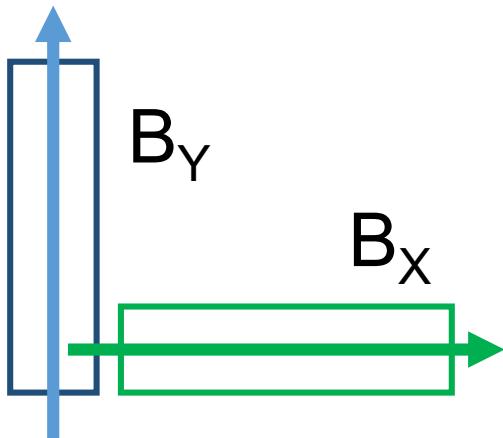


## Ex. 1: Electronic Compass

Earth's Magnetic Field Intensity :  $25\text{-}65 \mu\text{T}$  ( $0.25\text{--}0.65 \text{ G}$ )

Horizontal component in Pisa (from map)  $23300 \text{ nT} \sim 23 \mu\text{T}$





Sensor arrangement:  
Two orthogonal sensors that measures the X and Y (horizontal components) component of the magnetic field B

Angular resolution:

$$\theta_e = \frac{B_e}{|B_H|}$$

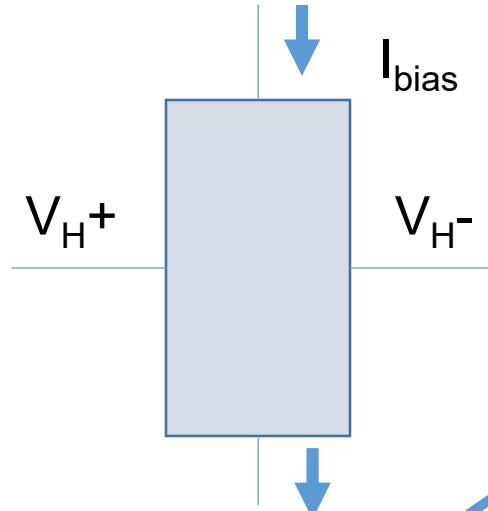
Let us consider a maximum error of  $5^\circ$  :

$$\theta_e = \frac{5}{180} \pi = 0.087 \text{ rad}$$

$$\max(B_e) = \max(\theta_e) |B_H| = 0.087 \cdot 28 \times 10^{-6} \text{ T} \cong 2 \text{ } \mu\text{T}$$

# Case 1: Use a couple of orthogonal Hall effect based on crystalline silicon

$$S_A = \frac{V_H}{B} = \frac{G \cdot r_H}{nqt} I_{bias}$$



$$R_0 = 2.2 \text{ k}\Omega$$

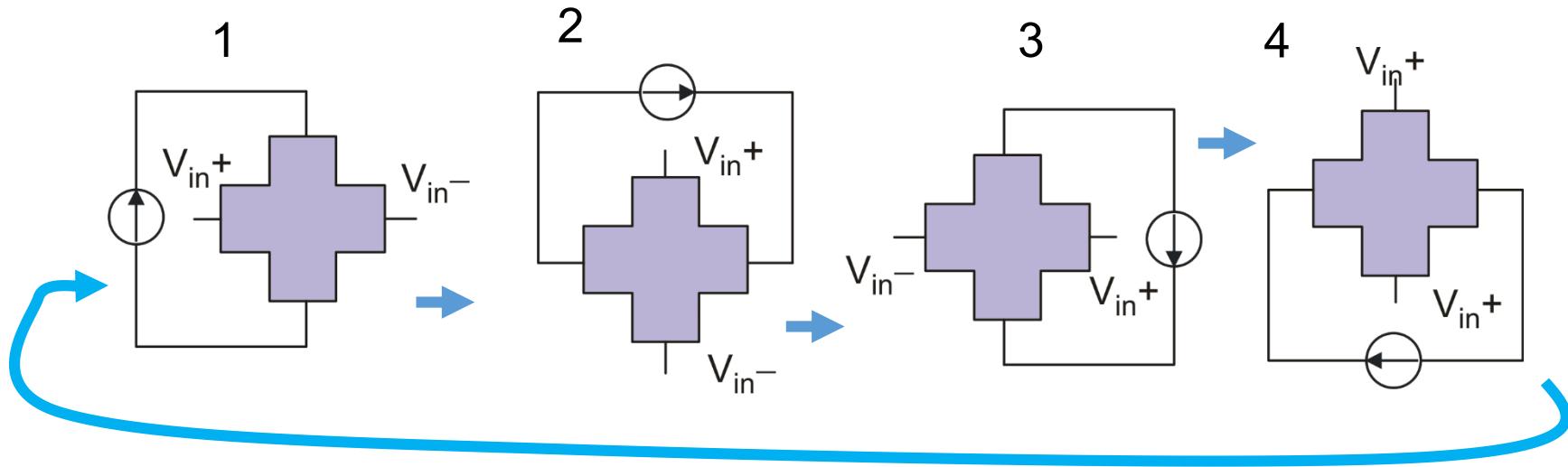
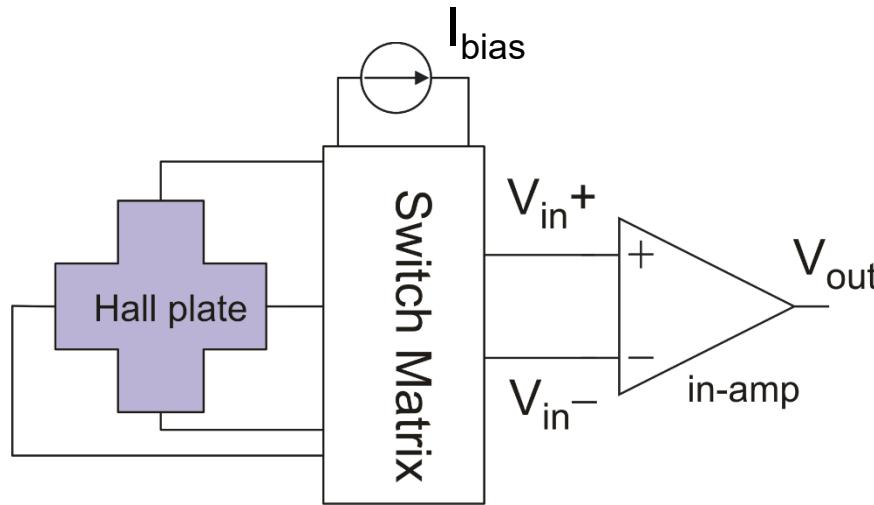
$$S_A = 0.0412 \text{ V/T}$$

**Table 1**  
Hall cells design parameters.

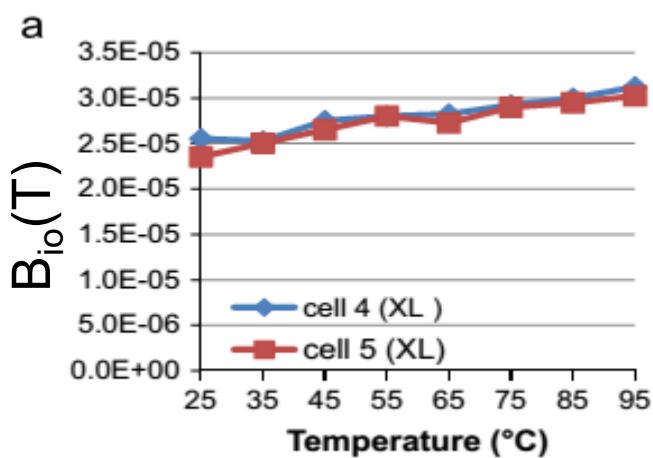
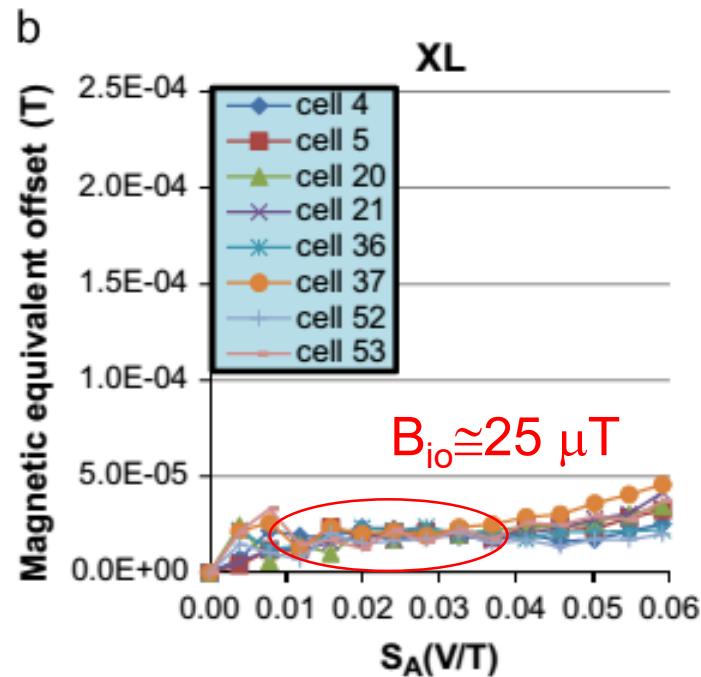
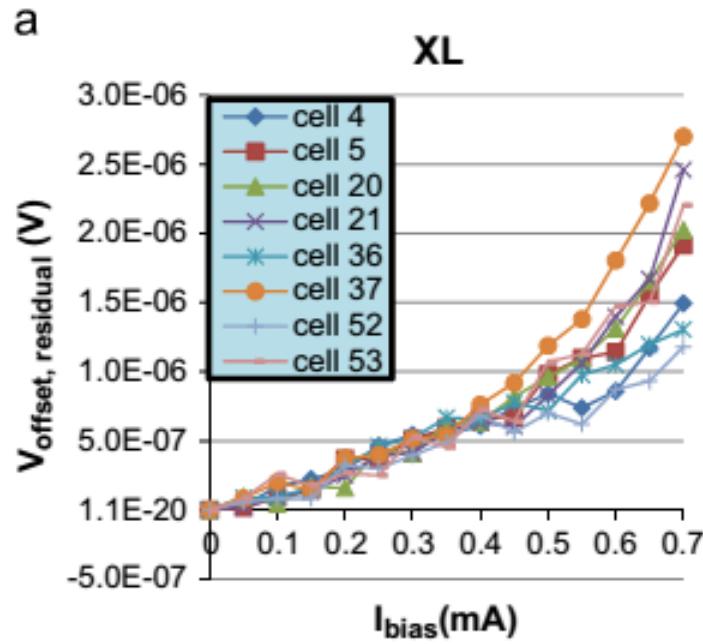
Hall cell	XL	Square
<b>Geometry (planar representation)</b>		
$R_0$ (k $\Omega$ ) @ $T=300$ K, $B=0$ T	2.2	4.9
$S_A$ (V/T) @ $I_{bias}=0.5$ mA	0.0412	0.0467
$L$ ( $\mu\text{m}$ )	43.2	20
$W$ ( $\mu\text{m}$ )	19	20
$L/W$	2.27	1
Contacts dimensions $s$ ( $\mu\text{m}$ )	18.3	2.3
Geometrical correction factor ( $G$ )	0.86	0.96

Typical readout approach for precise measurements:

## Current Spinning



# Sensor offset



$\Delta B_{io} < 5 \mu T$  (between 25 and 35 °C)

since  $2 \mu T \rightarrow 5^\circ$  angular error then:

Offset:  $\rightarrow 62.5^\circ$  angular error

Drift:  $\rightarrow 12.5^\circ$  angular error

## **Sensor noise**

**BW=0.1-100Hz**

$$S_{vR} = 4kTR_0 \quad R_0 = 2.2 \text{ k}\Omega$$

$$\sqrt{S_{vR}} = \sqrt{4kTR_0} = 5.93 \text{ nV}/\sqrt{\text{Hz}}$$

over 100 Hz BW:

$$V_{nS-\text{rms}} = 59.3 \text{ nV}$$

$$V_{nS-\text{pp}} = 237 \text{ nV}$$

$$B_{nS-pp} = \frac{V_{nS-pp}}{S_A} = 5.75 \text{ }\mu\text{T}$$

# Amplifier contribution to the angular error (1)

Case 1: AD 620. Offset: accuracy  
Noise: Resolution

Offset voltage (typ.) Input: 15  $\mu$ V Output 200  $\mu$ V

$$V_{\text{io-total}} = V_{\text{osi}} + V_{\text{oso}}/G \quad \text{with } G=1000 \quad V_{\text{io-total}} \approx V_{\text{osi}} = 15 \mu\text{V}$$

$V_{\text{osi}}$  drift (typ.) : 0.1 mV /  $^{\circ}\text{C}$  (**1  $\mu$ V** between 25 and 35  $^{\circ}\text{C}$ )

Offset current contribution:  $I_{\text{io}}R_0 = 0.3 \text{ nA} \times 2.2 \text{ k}\Omega = 0.66 \mu\text{V} \ll V_{\text{io-total}}$

Noise: BW 0.1-100 Hz

Broad Band noise:  $e_{\text{ni}} = \sqrt{S_{\text{VBB}}} = 9 \text{ nV} \sqrt{\text{Hz}} \rightarrow$  Integrated over BW=100Hz:

$$v_{\text{nBB-rms}} = 90 \text{ nV} \rightarrow v_{\text{nBB-pp}} = 360 \text{ nV}$$

Low frequency (Flicker) noise over 0.1-10 Hz  $\rightarrow 280 \text{ nV}$

Total noise voltage of the amplifier:

$$v_{nA-pp} = \sqrt{v_{\text{nBB-pp}}^2 + v_{\text{nF-pp}}^2} = 456 \text{ nV}$$

# Amplifier contribution to the angular error (2)

Current noise: Broad-band component

$$S_{VI} = 2S_I R_S^2 \quad R_S = \frac{R_0}{2} = 1.1 \text{ k}\Omega$$

$$\sqrt{S_{VI}} = \frac{\sqrt{S_I} R_0}{\sqrt{2}} \quad \sqrt{S_I} = 100 \text{ fA / } \sqrt{\text{Hz}}$$

$$\sqrt{S_{VI}} = 0.155 \text{ nV / } \sqrt{\text{Hz}}$$

Flicker component:

$$v_{ni-f-pp} = i_{n-pp} \frac{R_0}{\sqrt{2}} = 22 \text{ nV}$$

Noise voltage components due to the input bias current noise are negligible with respect to the input noise voltage components.

# Design of an electronic compass using the HMC 1002 Magneto-resistive sensor (2 axis)

Sensor characteristics:

V supply (typ) = 5 V

Output resistance: 850 Ω

Sensitivity: 3.2 mV/V/gauss SA=160 μV / μT (with V<sub>supply</sub> =5 V)

Noise:  $\sqrt{S_{VBB}} = 30 \text{ nV/}\sqrt{\text{Hz}}$  ;  $\sqrt{K_f} = 30 \text{ nV}$

Offset max: 60 mV

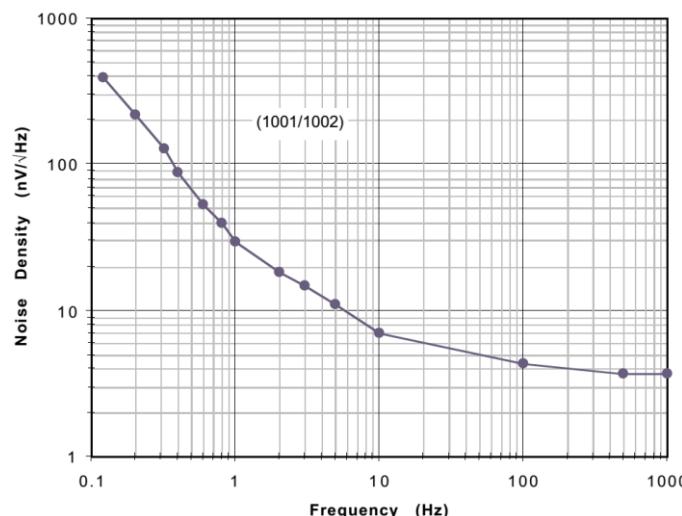


Figure 3—Typical Noise Density Curve

Offset: can be strongly reduced using the set-reset measurement cycle (see datasheet).  
The residual offset can be assumed to be given by the set-reset repeatability: 2μV

Noise:

BW 0.01 – 100 Hz (four decades)

$$v_{n-pp} = 4 \cdot e_n \cdot \sqrt{BW} \cong 1.6 \text{ } \mu\text{V} \quad \text{thermal}$$

$$v_{n-pp} = 4 \sqrt{k_f 2.3 \cdot n_{dec}} \cong 363 \text{ } \text{nV} \quad \text{flicker}$$

$$V_n = 1.64 \text{ } \mu\text{V p-p} \quad (\text{total})$$

Equivalent errors on the magnetic field:

$$B_{n-pp} = \frac{v_{n-pp}}{k_S} = \frac{1.6 \times 10^{-6}}{32 \times 10^{-6}} = 0.05 \text{ } \mu\text{T} \quad \text{Noise}$$

$$B_{io} = \frac{v_{io}}{k_S} = \frac{2 \times 10^{-6}}{32 \times 10^{-6}} = 0.062 \text{ } \mu\text{T} \quad \text{Offset}$$

## Conclusion

The offset and noise errors on the measured magnetic field is much smaller than the initial specification ( $2.4 \mu\text{T}$ ).

Therefore the sensor is suitable to obtain angular accuracies much better than the  $5^\circ$  specification.